

SOT-89 Plastic-Encapsulate Transistors

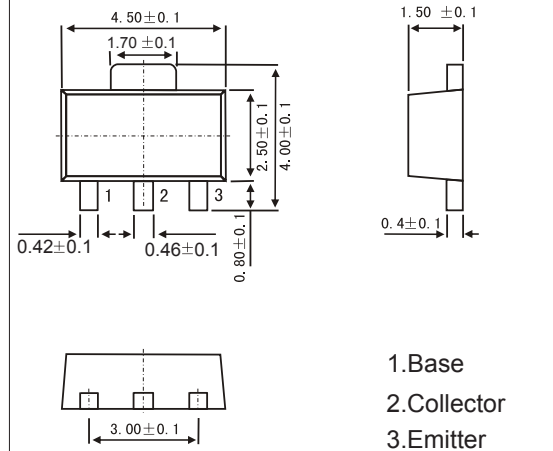
Features

- Switching and Linear Amplification
- High Current and Low Voltage
- Complement to PXT2222A
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any

SOT-89



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-60	V
Collector - Emitter Voltage	V _{CEO}	-60	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-600	mA
Collector Power Dissipation	P _C	500	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

PACKAGE INFORMATION

Device	Package	Shipping
PXT2907A (KXT2907A)	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -1 mA, I _E = 0	-60			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -10 mA, I _B = 0	-60			
Emitter - base breakdown voltage	V _{EB0}	I _E = -1 mA, I _C = 0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -50 V, I _E = 0			-50	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-50	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500 mA, I _B =-50mA			-1.6	V
		I _C =-500 mA, I _B =-15mA			-0.4	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-500 mA, I _B =-50mA			-2.6	
		I _C =-500 mA, I _B =-15mA			-1.3	
DC current gain	h _{FE(1)}	V _{CE} = -10V, I _C = -0.1mA	75			
	h _{FE(2)}	V _{CE} = -10V, I _C = -1mA	100			
	h _{FE(3)}	V _{CE} = -10V, I _C = -10mA	100			
	h _{FE(4)}	V _{CE} = -10V, I _C = -150mA	100		300	
	h _{FE(5)}	V _{CE} = -10V, I _C = -500mA	50			
Delay time	t _d	V _{CC} =-30V, I _C =-150mA I _{B1} =- I _{B2} = -15mA			12	ns
Rise time	t _r				30	
Storage time	t _s				300	
Fall time	t _f				65	
Transition frequency	f _T	V _{CE} = -10V, I _C = -20mA, f=100MHz	200			MHz

Marking

Marking	*2F
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